## **MDD44-14N1B**

## **Standard Rectifier Module**

Phase	lea
Phase	leg

Part number

MDD44-14N1B





Backside: isolated **E**72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- · Very low leakage current

### **Applications:**

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

### Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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## MDD44-14N1B

Rectifier					Rating	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1500	V
V <sub>RRM</sub>	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1400	V
I <sub>R</sub>	reverse current	$V_{R} = 1400 V$	$T_{VJ} = 25^{\circ}C$			100	μA
		$V_{R} = 1400 V$	$T_{vJ} = 150^{\circ}C$			10	mA
VF	forward voltage drop	I <sub>F</sub> = 100 A	$T_{VJ} = 25^{\circ}C$			1.30	V
		I <sub>F</sub> = 200 A				1.60	V
		$I_{F} = 100 \text{ A}$	T <sub>VJ</sub> = 125 °C			1.26	V
		I <sub>F</sub> = 200 A				1.67	v
FAV	average forward current	T <sub>c</sub> = 100°C	T <sub>vJ</sub> = 150°C			59	Α
F(RMS)	RMS forward current	180° sine				100	Α
V <sub>F0</sub>	threshold voltage		T <sub>vj</sub> = 150°C			0.80	V
r <sub>F</sub>	slope resistance } for power	loss calculation only				4.3	mΩ
<b>R</b> <sub>thJC</sub>	thermal resistance junction to ca	ase				0.59	K/W
R <sub>thCH</sub>	thermal resistance case to heats	sink			0.20		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			212	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.15	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.24	kA
		t = 10 ms; (50 Hz), sine	T <sub>vj</sub> = 150°C			980	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.06	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			6.62	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			6.40	kA²s
		t = 10 ms; (50 Hz), sine	T <sub>vJ</sub> = 150°C			4.80	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			4.63	kA²s
C	junction capacitance	V <sub>B</sub> = 400 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		27		pF

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## MDD44-14N1B

Package	TO-240AA				F	Ratings	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T <sub>vj</sub>	virtual junction temperature				-40		150	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						76		g
M <sub>D</sub>	mounting torque				2.5		4	Nm
M <sub>T</sub>	terminal torque				2.5		4	Nm
d <sub>Spp/App</sub>	croopago dictanco on curfac	o / striking distance through air	terminal to terminal	13.0	9.7			mm
<b>d</b> <sub>Spb/Apb</sub>	creepage distance on surface   striking distance through a		terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
	t = 1 minut		50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD44-14N1B	MDD44-14N1B	Box	36	458031

Similar Part	Package	Voltage class
MDD44-08N1B	TO-240AA	800
MDD44-12N1B	TO-240AA	1200
MDD44-16N1B	TO-240AA	1600
MDD44-18N1B	TO-240AA	1800

Equiva	lent Circuits for	Simulation	* on die level	$T_{vJ} = 150 \text{ °C}$
	$-R_{o}$	Rectifier		
$V_{0 \text{ max}}$	threshold voltage	0.8		V
$\mathbf{R}_{0 \max}$	slope resistance *	3.1		mΩ

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Outlines TO-240AA







DC

60° 30°

100

T<sub>c</sub> [°C]

150

200

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180° sin 120°



Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive load

0

50

T<sub>▲</sub> [°C]

100

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50

 $I_{dAVM}$  [A]

150

100

0

0

## MDD44-14N1B

### Rectifier







rig. / Transform information podation to babe (per diode)	Fig. 7	Transient thermal impedance junction to case (per diode)
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R <sub>th</sub>	<sub>JK</sub> for vario	us conduction angles d:
	d R <sub>th</sub>	<sub>JK</sub> [K/W]
	DC	0.79
	180°	0.81
	120°	0.83
	60°	0.86
	30°	0.90
Co	nstants fo	$r Z_{thJK}$ calculation:
i	R <sub>thi</sub> [K/W]	t <sub>i</sub> [s]
1	0.012	0.0012
2	0.045	0.0950
3	0.533	0.4550
4	0.200	0.4950

 ${\rm R}_{\rm thJC}$  for various conduction angles d:

d  $R_{thJC}$  [K/W]

0.59

0.61

0.63

0.66

0.70

Constants for  $Z_{thJC}$  calculation:

t<sub>i</sub> [s]

0.0012

0.0950

0.4550

DC

180°

120°

60°

30°

i R<sub>thi</sub> [K/W]

1 2

3

0.012

0.045

0.533

Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

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